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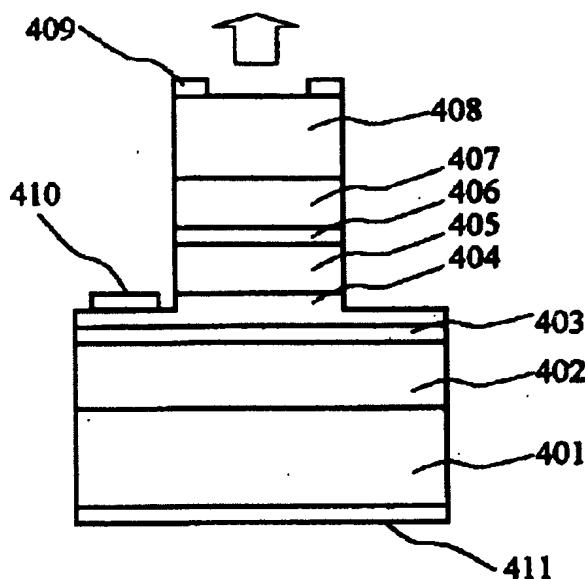
APPLICATION DATE : 18-01-02
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APPLICANT : RICOH CO LTD;

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TITLE : SEMICONDUCTOR LIGHT EMITTING
DEVICE AND METHOD OF
MANUFACTURING THE SAME, AND
OPTICAL TRANSMISSION SYSTEM



ABSTRACT : PROBLEM TO BE SOLVED: To suppress the deterioration of a light emitting characteristic and a surface property of a semiconductor light emitting device which is such that a surface type semiconductor light modulator is integrated inside a surface emitting semiconductor laser device.

SOLUTION: Between a crystal growth process of a GaAs/AlGaAs lower distributed Bragg reflector 402 of a first conductivity type and a crystal growth process of a GaInNAs light absorption layer 403, a process for removing an Al material remaining in a place to be brought into contact with a nitride compound material in a growth chamber or with an impurity contained in the nitride compound material, an Al reactant, an Al compound, or Al is set up.

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